

PNP High Power Bipolar Transistor

Features

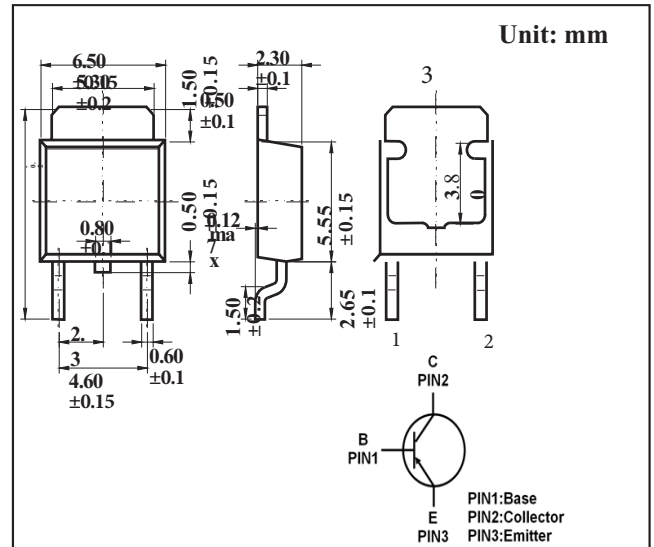
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Complement to MJD122
- High DC Current Gain

Mechanical Data

- Package: TO-252
- Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- Unit Weight: 0.32g


Maximum Ratings (Ta=25°C unless otherwise noted)

Item	Symbol	Unit	Value
Device marking code			MJD127
Collector-base voltage	V_{CBO}	V	-100
Collector-emitter voltage	V_{CEO}	V	-100
Emitter-base voltage	V_{EBO}	V	-5
Collector current	I_C	A	-5
Power dissipation(Note1)	P_D	W	1.5
Thermal resistance, junction-to-ambient (°)	R_{thJA}	°C/W	83.3
Junction temperature	T_j	°C	-55 to +150
Storage temperature	T_{STG}	°C	-55 to +150

Note1: The data tested by surface mounted on a 40*40*1.1mm heatsink.

■ Electrical Characteristics (Ta=25°C unless otherwise noted)

Item	Symbol	Unit	Conditions	Min	Typ	Max
Collector-base breakdown voltage	$V_{(BR)CBO}$	V	$I_C=-1mA, I_E=0$	-100		
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	V	$I_C=-30mA, I_B=0$	-100		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	V	$I_E=-2mA, I_C=0$	-5		
Collector-base cut-off current	I_{CBO}	mA	$V_{CB}=-100V$			-0.2
Collector cutoff current	I_{CEO}	mA	$V_{CE}=-30V$			-0.5
Emitter-base cut-off current	I_{EBO}	mA	$V_{EB}=-5V$			-2
DC current gain	h_{FE}		$V_{CE}=-3V, I_C=-0.5A$	1000		
			$V_{CE}=-3V, I_C=-3A$	1000		
Collector-emitter saturation voltage	$V_{CE(sat)}$	V	$I_C=-3A, I_B=-12mA$			-2.0
			$I_C=-5A, I_B=-20mA$			-4.0
Base-Emitter Voltage	V_{BE}	V	$V_{CE}=-3V, I_C=-3A$			-2.5
Collector-base output capacitance	C_{ob}	pF	$V_{CB}=-10V, I_E=0A, f=1MHz$		88	

■ Characteristics(Typical)

